

30V P-Channel Enhancement Mode MOSFET

$V_{DS} = -30V$

$R_{DS(ON)}, V_{GS} @ -10V, I_{DS} @ -4.2A < 64m\Omega$

$R_{DS(ON)}, V_{GS} @ -4.5V, I_{DS} @ -4.0A < 75m\Omega$

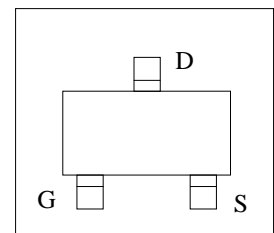
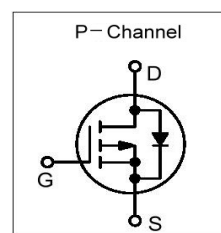
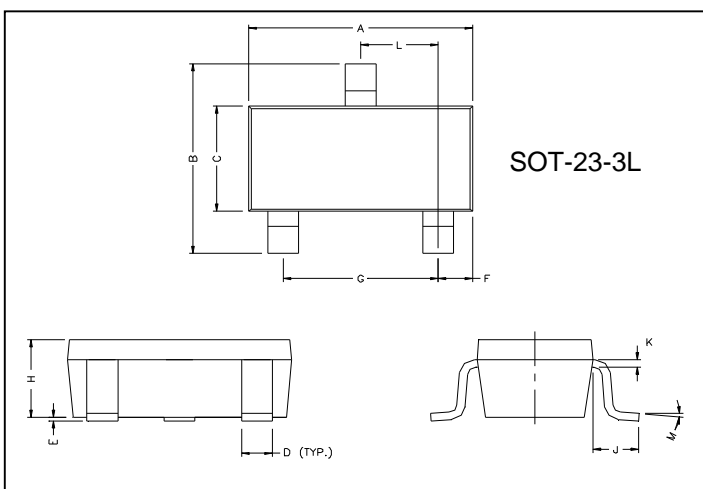
$R_{DS(ON)}, V_{GS} @ -2.5V, I_{DS} @ -1.0A < 120m\Omega$

Features

Advanced trench process technology

High Density Cell Design For Ultra Low On-Resistance

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.65	2.95	H	1.00	1.30
C	1.50	1.70	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

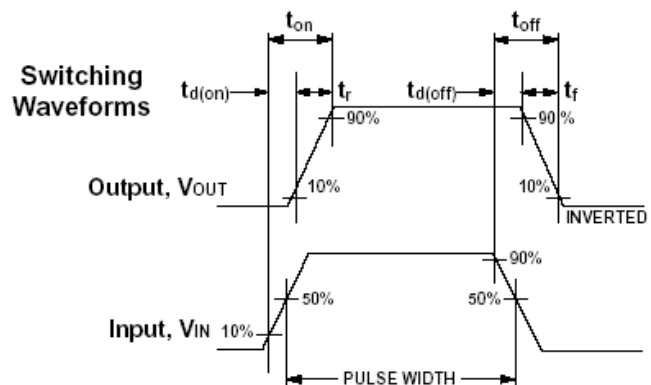
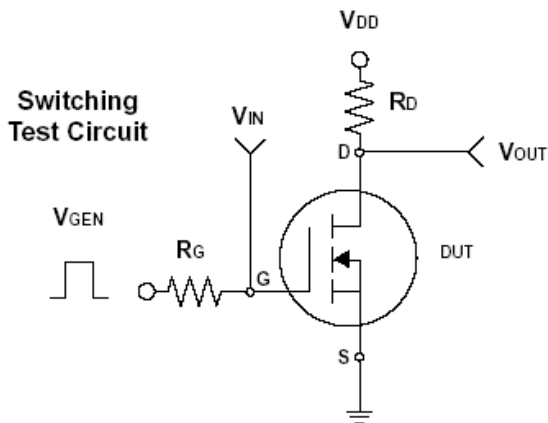
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	-30	V	
Gate-Source Voltage	V_{GS}	±12		
Continuous Drain Current	I_D	-4.2	A	
Pulsed Drain Current	I_{DM}	-30		
Maximum Power Dissipation	P_D	TA = 25°C	1.4	W
		TA = 75°C	1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	°C	
Junction-to-Ambient Thermal Resistance (PCB mounted)	$R_{\theta JA}$	125	°C/W	

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ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.2A$		42.0	64.0	mΩ
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$		64.0	75.0	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -2.5V, I_D = -1A$		80.0	120.0	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.7	-1	-1.3	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
Gate Body Leakage	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Forward Transconductance	g_{fs}	$V_{DS} = -5V, I_D = -5A$	7	11	—	S
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 20V, I_D = 5.7A$ $V_{GS} = 10V$		9.4		nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20V, R_L = 20\Omega$ $I_D = 1A, V_{GEN} = 10V$ $R_G = 6\Omega$		6.3		ns
Turn-On Rise Time	t_r			3.2		
Turn-Off Delay Time	$t_{d(off)}$			38.2		
Turn-Off Fall Time	t_f			12		
Input Capacitance	C_{iss}	$V_{DS} = 8V, V_{GS} = 0V$ $f = 1.0\text{ MHz}$		954		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			77		
Source-Drain Diode						
Max. Diode Forward Current	I_S				-2.2	A
Diode Forward Voltage	V_{SD}	$I_S = 1.8A, V_{GS} = 0V$			-1.0	V

Note: Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%



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Typical Characteristics (T_J = 25°C Noted)

